

PATENT ABSTRACTS OF JAPAN

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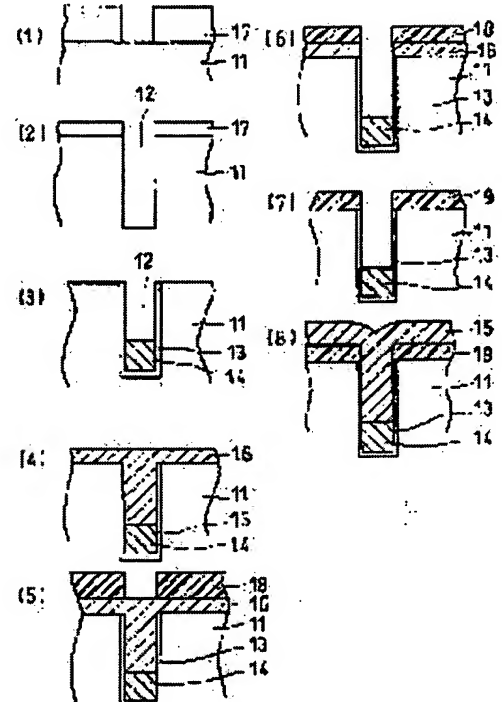
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(54) MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To obtain a semiconductor device manufacturing method capable of improving a film work in processing accuracy, when the stepped part of the film work is processed by a method where the material or thickness of a mask of an etching stopping layer is selected in a wide range.

SOLUTION: This semiconductor device manufacturing method comprises a process, where a processed layer 11 with a stepped part 12 is processed, a mask layer 19 or an etching stopper layer is formed on the stepped part 12 provided to the processed layer 11, and the process is carried out by the use of the mask layer 19 or the stopper layer.



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